AMENDMENTS TO THE SPECIFICATION

Please amend the following paragraph at page 3, lines 11-18 as follows:

The capacitor contact hole is ~~stuffed~~ filled with a plug material such as a poly-silicon while the plug material is deposited over an entire upper part of the substrate. As a result, a second plug is formed and electrically gets to be in contact with the first plug. Another CMP process is carried out to perform a planarization process for an upper part of the semiconductor substrate which has gone through the predetermined processes.

Please amend the following paragraph at page 6, lines 15-17 as follows:

Accordingly, a line width of the lower electrode 22 becomes finer and therefore, the electrical short of the neighboring lower electrodes takes place more frequently as shown at 23.

Please amend the following paragraph at page 17, lines 8-18 as follows:

Figs. 7 (A) (B) (C) are schematic cross-sectional views of the lower electrode 62 respectively shown along an X1 imaginary line, an Y1" imaginary line and a Z-Z' imaginary line shown in Fig. 6. When the lower electrodes 62 having octagonal or circular cylinder structure are applied to the semiconductor device, the capacitance of the capacitor can be improved and the bowing phenomenon of the sacrifice insulation layer caused by an excessive etching process is prevented because the aspect ratio of the major and minor axes of the lower electrodes 62 having the octagonal or circular cylinder structure is about 1 to 1.